

semitransparent phase shifting film, said phase shifting film being formed at a predetermined position on a photomask substrate and having a transmittance with respect to exposure light not higher than 25% and (b) a light shielding area provided at a peripheral edge portion of said first semitransparent phase shifting pattern and serving to make an intensity of light having passed through said light shielding area smaller than an intensity of light having passed through said semitransparent phase shifting film, as measured on a to-be-exposed film;

exposing a first area of said to-be-exposed film by use of said semitransparent phase shifting mask;

moving said sample stage in a horizontal direction; and exposing a second area, different from said first area, of said to-be-exposed film by use of said semitransparent phase shifting mask.

43. (Amended) A method according to claim 42, wherein said light shielding area includes a second semitransparent phase shifting pattern having a semitransparent phase shifting portion and a transparent portion, said second semitransparent phase shifting pattern being comprised of a pattern beyond a critical resolution of an exposure apparatus.